

**Notice of References Cited**Application/Control No.  
09/332,271Applicant(s)/Patent Under  
Reexamination  
SCHUEGRAF ET AL.Examiner  
Ron E PompeyArt Unit  
2812

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number	Date	Name	Classification	
		Country Code-Number-Kind Code	MM-YYYY			
	A	US-5439833	08-1995	Herbert et al.	--	--
	B	US-				
	C	US-				
	D	US-				
	E	US-				
	F	US-				
	G	US-				
	H	US-				
	I	US-				
	J	US-				
	K	US-				
	L	US-				
	M	US-				

**FOREIGN PATENT DOCUMENTS**

*		Document Number	Date	Country	Name	Classification	
		Country Code-Number-Kind Code	MM-YYYY				
	N	JP-401276761-A	11-1989	Japan	Nonaka	--	--
	O						
	P						
	Q						
	R						
	S						
	T						

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	.Ku et al. ; "The application of ion-beam mixing, doped silicide, and rapid thermal processing self-aligned silicide technology", VLSI Technology, Systems and Applications, May 17-19, 1989, Pages 337-341
	V	Lange, H.; "Physical Properties of Semiconducting Transition Metal Silicides and their Prospects in Si-Based Device Applications"; IEEE 1998; pages 247-250.
	W	Mogami et al. ; " Low- Resistance Self-Alignned Ti-Silicide Technology for Sub-Quarter Micron CMOS Devices"; IEEE 1996; pages 932-939
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.